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AAP Gen 7 (TO-240AA) Power Modules Thyristor/Diode and Thyristor/Thyristor, 95 A



ADD-A-PAK

PRIMARY CHARACTERISTICS			
$I_{T(AV)}$ or $I_{F(AV)}$	95 A		
Туре	Modules - thyristor, standard		
Package	AAP Gen 7 (TO-240AA)		

MECHANICAL DESCRIPTION

The AAP Gen 7 (TO-240AA), new generation of AAP module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

FEATURES

- High voltage
- Industrial standard package
- Low thermal resistance
- UL approved file E78996
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- High surge capability
- Easy mounting on heatsink

ELECTRICAL DESCRIPTION

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATINGS	MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS				
I _{T(AV)} or I _{F(AV)}	85 °C	95					
I _{O(RMS)}	As AC switch	210	А				
I _{TSM,}	50 Hz	2000	A				
I _{FSM}	60 Hz	2094					
l ² t	50 Hz	20	kA ² s				
1-1	60 Hz	18.26	NA-5				
l²√t		200	kA²√s				
V _{RRM}	Range	400 to 1600	V				
T _{Stg}		-40 to +125	°C				
TJ		-40 to +125	°C				



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ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS						
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I _{RRM,} I _{DRM} AT 125 °C mA	
	04	400	500	400		
	06	600	700	600		
	08	800	900	800		
VS-VSK.91	10	1000	1100	1000	15	
	12	1200	1300	1200		
	14	1400	1500	1400		
	16	1600	1700	1600		

ON-STATE CONDUCTION						
PARAMETER	SYMBOL		TEST COND	TIONS	VALUES	UNITS
Maximum average on-state current (thyristors)	I _{T(AV)}	N) 180° conduction, half sine wave,		95		
Maximum average forward current (diodes)	I _{F(AV)}	T _C = 85 °C			90	
Maximum continuous RMS on-state current, as AC switch	I _{O(RMS)}	•	F ↓ I _(RMS) or ∽	↓ ↓ ↓ (RMS)	210	А
		t = 10 ms	No voltage		2000	
Maximum peak, one-cycle non-repetitive	ITSM	t = 8.3 ms	reapplied	Sinusoidal	2094	
on-state or forward current	or I _{FSM}	t = 10 ms	100 % V _{RRM}	half wave, initial T _J = T _J maximum	1682	
	1 310	t = 8.3 ms	reapplied		1760	
		t = 10 ms	No voltage		20	kA ² s
Maximum I ² t for fusing	l ² t	t = 8.3 ms	reapplied		18.26	
	1-1	t = 10 ms	100 % V _{RBM}	Initial $T_J = T_J$ maximum	14.14	
		t = 8.3 ms	reapplied		12.91	
Maximum I ² \sqrt{t} for fusing	l²√t (1)	t = 0.1 ms to 1 T _J = T _J maxim	0 ms, no voltag um	e reapplied	200	kA²√s
Maximum value or threshold valtage	V (2)	Low level (3)	T T mavin		0.97	V
Maximum value or threshold voltage	V _{T(TO)} ⁽²⁾	High level ⁽⁴⁾	$T_J = T_J maxin$	lum	1.1	v
Maximum value of on-state	r _t ⁽²⁾	Low level (3)	T T marin		2.76	
slope resistance	r _t (=)	High level ⁽⁴⁾	$T_J = T_J maxin$	hum	2.38	mΩ
	V _{TM}	$I_{TM} = \pi \times I_{T(AV)}$	T 05 %C		1.73	V
Maximum peak on-state or forward voltage	V _{FM}	$I_{FM} = \pi \times I_{F(AV)}$	$1_1 = 25 ^{\circ}\text{C}$		1.73	v
Maximum non-repetitive rate of rise of turned on current	dl/dt	T_J = 25 °C, from 0.67 V _{DRM} , I _{TM} = π x I _{T(AV)} , I _g = 500 mA, t _r < 0.5 μs, t _p > 6 μs		150	A/µs	
Maximum holding current	I _H	$T_J = 25$ °C, anode supply = 6 V, resistive load, gate open circuit			250	mA
Maximum latching current	١L	$T_J = 25 \text{ °C}, \text{ and}$	ode supply = 6 V	V, resistive load	400	

Notes

⁽¹⁾ I²t for time $t_x = I^2 \sqrt{t} x \sqrt{t_x}$

 $^{(2)}$ Average power = V_{T(TO)} x I_{T(AV)} + r_t x (I_{T(RMS)})^2

⁽³⁾ 16.7 % x π x $I_{AV} < I < \pi$ x I_{AV}

(4) $I > \pi x I_{AV}$

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TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum peak gate power	P _{GM}			12	W	
Maximum average gate power	P _{G(AV)}			3.0	vv	
Maximum peak gate current	I _{GM}			3.0	А	
Maximum peak negative gate voltage	- V _{GM}			10		
		T _J = -40 °C	Anode supply = 6 V resistive load	4.0	v	
Maximum gate voltage required to trigger	V _{GT}	T _J = 25 °C		2.5		
		T _J = 125 °C		1.7		
		T _J = -40 °C		270	mA	
Maximum gate current required to trigger	I _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	150		
		T _J = 125 °C		80		
Maximum gate voltage that will not trigger	V _{GD}	T _J = 125 °C, rated V _{DRM} applied		0.25	V	
Maximum gate current that will not trigger	I _{GD}	$T_J = 125 \text{ °C}, \text{ rated } V_{DRM}$	applied	6	mA	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak reverse and off-state leakage current at V_{RRM} , V_{DRM}	I _{RRM,} I _{DRM}	T _J = 125 °C, gate open circuit	15	mA	
Maximum RMS insulation voltage	V _{INS}	50 Hz	3000 (1 min) 3600 (1 s)	V	
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = 125 \text{ °C}$, linear to 0.67 V_{DRM}	1000	V/µs	

THERMAL AND MECH	THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER SYM		SYMBOL	SYMBOL TEST CONDITIONS		UNITS	
Junction operating and storage temperature range		T _J , T _{Stg}		-40 to +125	°C	
Maximum internal thermal resist junction to case per leg	ance,	R _{thJC}	DC operation	0.22	°C/W	
Typical thermal resistance, case to heatsink per module	Ś Bu		Mounting surface flat, smooth and greased	0.1	C/W	
Mounting torque + 10.%	to heatsink		A mounting compound is recommended and the torgue should be rechecked after a period of	4	Nm	
Mounting torque ± 10 %busbar			3 hours to allow for the spread of the compound.	3	INITI	
Approvinceto weight				75	g	
Approximate weight	Approximate weight			2.7	oz.	
Case style			JEDEC®	AAP Gen 7	(TO-240AA)	

DEVICES	5	SINE HALF WAVE CONDUCTION				RECTANGULAR WAVE CONDUCTION					
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30 °	UNITS
VSK.91	0.04	0.048	0.063	0.085	0.125	0.033	0.052	0.067	0.088	0.127	°C/W

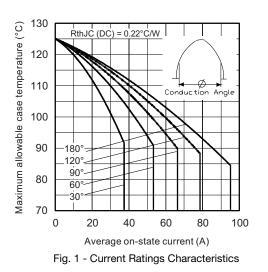
Note

Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

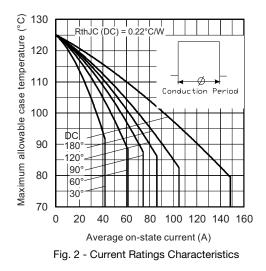
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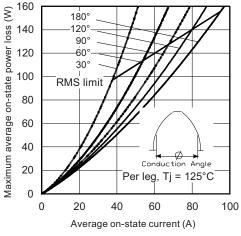
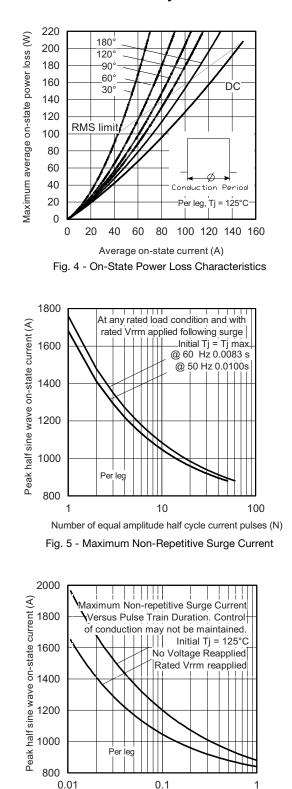


Fig. 3 - On-State Power Loss Characteristics





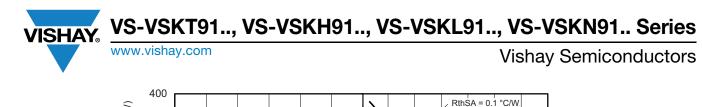
Pulse train duration (s)

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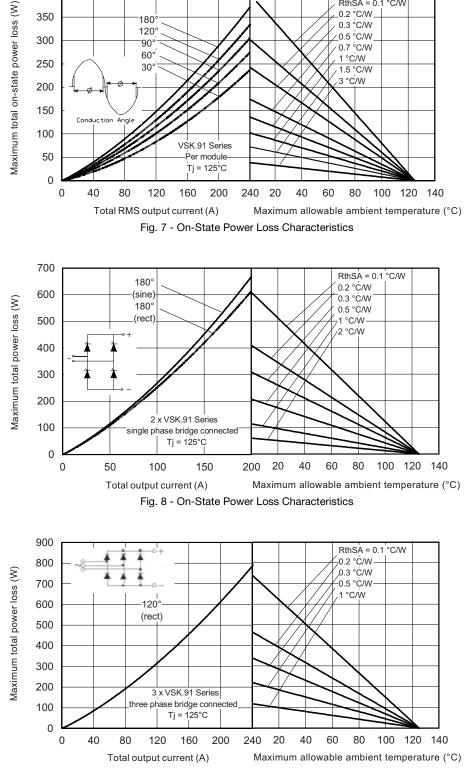


Fig. 9 - On-State Power Loss Characteristics

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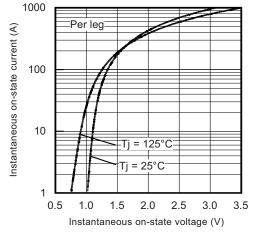
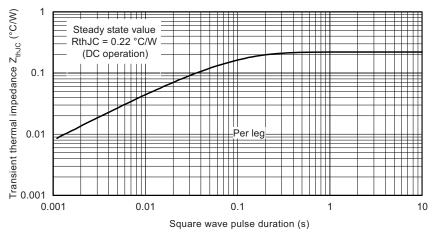
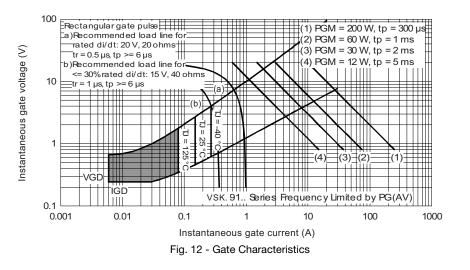


Fig. 10 - On-State Voltage Drop Characteristics





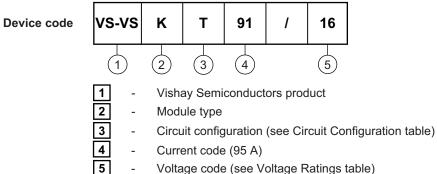


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ORDERING INFORMATION TABLE



Note

To order the optional hardware go to www.vishay.com/doc?95172

CIRCUIT CONFIGURATION	CIRCUIT CONFIGURATION					
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING				
Two SCRs doubler circuit	т					
SCR/diode doubler circuit, positive control	н					
SCR/diode doubler circuit, negative control	L	VSKL				
SCR/diode common anodes	Ν					

LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95368		
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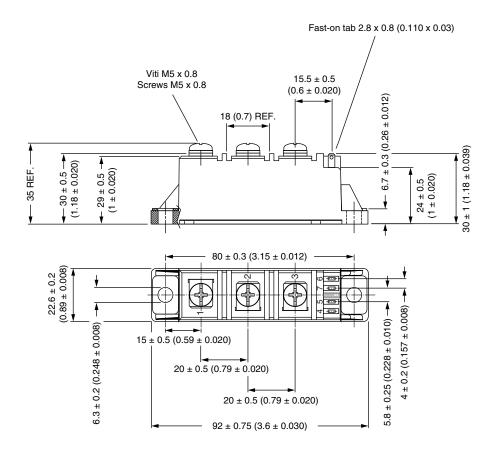
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ADD-A-PAK Generation VII - Thyristor

DIMENSIONS in millimeters (inches)

SHA





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